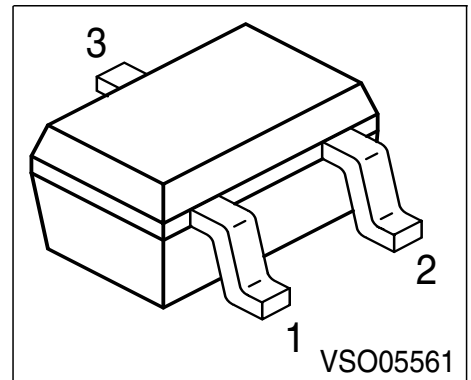


**NPN Silicon RF Transistor**

- For low noise, high-gain broadband amplifiers at collector currents from 1 mA to 20 mA
- $f_T = 8 \text{ GHz}$   
 $F = 1.2 \text{ dB at } 900 \text{ MHz}$



**ESD:** Electrostatic discharge sensitive device, observe handling precaution!

| Type     | Marking | Pin Configuration |       |       | Package |
|----------|---------|-------------------|-------|-------|---------|
| BFR 182W | RGs     | 1 = B             | 2 = E | 3 = C | SOT-323 |

**Maximum Ratings**

| Parameter                                                          | Symbol    | Value       | Unit |
|--------------------------------------------------------------------|-----------|-------------|------|
| Collector-emitter voltage                                          | $V_{CEO}$ | 12          | V    |
| Collector-emitter voltage                                          | $V_{CES}$ | 20          |      |
| Collector-base voltage                                             | $V_{CBO}$ | 20          |      |
| Emitter-base voltage                                               | $V_{EBO}$ | 2           |      |
| Collector current                                                  | $I_C$     | 35          | mA   |
| Base current                                                       | $I_B$     | 4           |      |
| Total power dissipation, $T_S \leq 90^\circ\text{C}$ <sup>F)</sup> | $P_{tot}$ | 250         | mW   |
| Junction temperature                                               | $T_j$     | 150         | °C   |
| Ambient temperature                                                | $T_A$     | -65 ... 150 |      |
| Storage temperature                                                | $T_{stg}$ | -65 ... 150 |      |

**Thermal Resistance**

|                            |            |            |     |
|----------------------------|------------|------------|-----|
| Junction - soldering point | $R_{thJS}$ | $\leq 240$ | K/W |
|----------------------------|------------|------------|-----|

<sup>1</sup>  $T_S$  is measured on the collector lead at the soldering point to the pcb

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

| Parameter                                                              | Symbol        | Values |      |      | Unit          |
|------------------------------------------------------------------------|---------------|--------|------|------|---------------|
|                                                                        |               | min.   | typ. | max. |               |
| DC characteristics                                                     |               |        |      |      |               |
| Collector-emitter breakdown voltage<br>$I_C = 1\text{ mA}, I_B = 0$    | $V_{(BR)CEO}$ | 12     | -    | -    | V             |
| Collector-emitter cutoff current<br>$V_{CE} = 20\text{ V}, V_{BE} = 0$ | $I_{CES}$     | -      | -    | 100  | $\mu\text{A}$ |
| Collector-base cutoff current<br>$V_{CB} = 10\text{ V}, I_E = 0$       | $I_{CBO}$     | -      | -    | 100  | nA            |
| Emitter-base cutoff current<br>$V_{EB} = 1\text{ V}, I_C = 0$          | $I_{EBO}$     | -      | -    | 1    | $\mu\text{A}$ |
| DC current gain<br>$I_C = 10\text{ mA}, V_{CE} = 8\text{ V}$           | $h_{FE}$      | 50     | 100  | 200  | -             |

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

| Parameter                                                                                                                                                   | Symbol        | Values |            |        | Unit |
|-------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|--------|------------|--------|------|
|                                                                                                                                                             |               | min.   | typ.       | max.   |      |
| AC characteristics (verified by random sampling)                                                                                                            |               |        |            |        |      |
| Transition frequency<br>$I_C = 15\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $f = 500\text{ MHz}$                                                                 | $f_T$         | 6      | 8          | -      | GHz  |
| Collector-base capacitance<br>$V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$                                                                                   | $C_{cb}$      | -      | 0.4        | 0.65   | pF   |
| Collector-emitter capacitance<br>$V_{CE} = 10\text{ V}$ , $f = 1\text{ MHz}$                                                                                | $C_{ce}$      | -      | 0.24       | -      |      |
| Emitter-base capacitance<br>$V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$                                                                                    | $C_{eb}$      | -      | 0.6        | -      |      |
| Noise figure<br>$I_C = 3\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ ,<br>$f = 900\text{ MHz}$<br>$f = 1.8\text{ GHz}$                            | $F$           | -<br>- | 1.2<br>1.9 | -<br>- | dB   |
| Power gain, maximum stable <sup>F)</sup><br>$I_C = 10\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ ,<br>$f = 900\text{ MHz}$    | $G_{ms}$      | -      | 19         | -      |      |
| Power gain, maximum available <sup>F)</sup><br>$I_C = 10\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ ,<br>$f = 1.8\text{ GHz}$ | $G_{ma}$      | -      | 12.5       | -      |      |
| Transducer gain<br>$I_C = 10\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_L = 50\Omega$ ,<br>$f = 900\text{ MHz}$<br>$f = 1.8\text{ GHz}$                  | $ S_{21e} ^2$ | -<br>- | 15<br>9.5  | -<br>- |      |

$$^1G_{ms} = |S_{21} / S_{12}|$$

$$^2G_{ma} = |S_{21} / S_{12}| (k - (k^2 - 1)^{1/2})$$

## Transistor Chip Data

|       |         |          |       |          |          |        |          |          |
|-------|---------|----------|-------|----------|----------|--------|----------|----------|
| IS =  | 4.8499  | fA       | BF =  | 84.113   | -        | NF =   | 0.56639  | -        |
| VAF = | 21.742  | V        | IKF = | 0.14414  | A        | ISE =  | 8.4254   | fA       |
| NE =  | 0.91624 | -        | BR =  | 10.004   | -        | NR =   | 0.54818  | -        |
| VAR = | 2.2595  | V        | IKR = | 0.039478 | A        | ISC =  | 5.9438   | fA       |
| NC =  | 0.5641  | -        | RB =  | 2.8263   | $\Omega$ | IRB =  | 0.071955 | mA       |
| RBM = | 3.4217  | $\Omega$ | RE =  | 2.1858   |          | RC =   | 1.8159   | $\Omega$ |
| CJE = | 8.8619  | fF       | VJE = | 1.0378   | V        | MJE =  | 0.40796  | -        |
| TF =  | 22.72   | ps       | XTF = | 0.43147  | -        | VTF =  | 0.34608  | V        |
| ITF = | 6.5523  | mA       | PTF = | 0        | deg      | CJC =  | 490.25   | fF       |
| VJC = | 1.0132  | V        | MJC = | 0.31068  | -        | XCJC = | 0.19281  | -        |
| TR =  | 1.7541  | ns       | CJS = | 0        | fF       | VJS =  | 0.75     | V        |
| MJS = | 0       | -        | XTB = | 0        | -        | EG =   | 1.11     | eV       |
| XTI = | 3       | -        | FC =  | 0.64175  | -        | TNOM   | 300      | K        |

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The diagram shows an equivalent circuit for a transistor model. A central box labeled "Transistor Chip" has three terminals: B' (base), C' (collector), and E' (emitter). The base terminal B' is connected to an input port B through an inductor  $L_{BO}$ . A capacitor  $C_{BE}$  is connected between B' and E'. The collector terminal C' is connected to an output port C through an inductor  $L_{CO}$ . A capacitor  $C_{CE}$  is connected between C' and E'. The emitter terminal E' is connected to an output port E through an inductor  $L_{EO}$ . A capacitor  $C_{CB}$  is connected between B' and C'. Inductors  $L_{BI}$  and  $L_{CI}$  are connected between B' and C' and between C' and E' respectively. The circuit is labeled EHA07222.

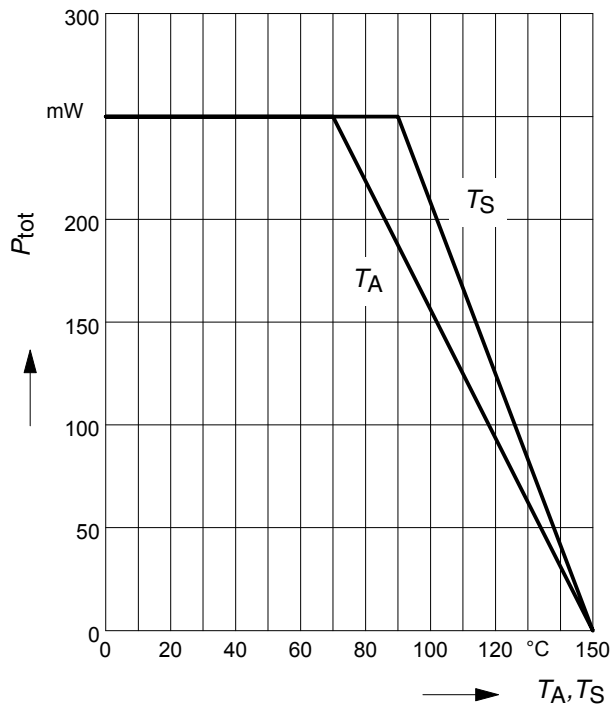
|            |      |    |
|------------|------|----|
| $L_{BI} =$ | 0.57 | nH |
| $L_{BO} =$ | 0.4  | nH |
| $L_{EI} =$ | 0.43 | nH |
| $L_{EO} =$ | 0.5  | nH |
| $L_{CI} =$ | 0    | nH |
| $L_{CO} =$ | 0.41 | nH |
| $C_{BE} =$ | 61   | fF |
| $C_{CB} =$ | 101  | fF |
| $C_{CE} =$ | 175  | fF |

Valid up to 6GHz

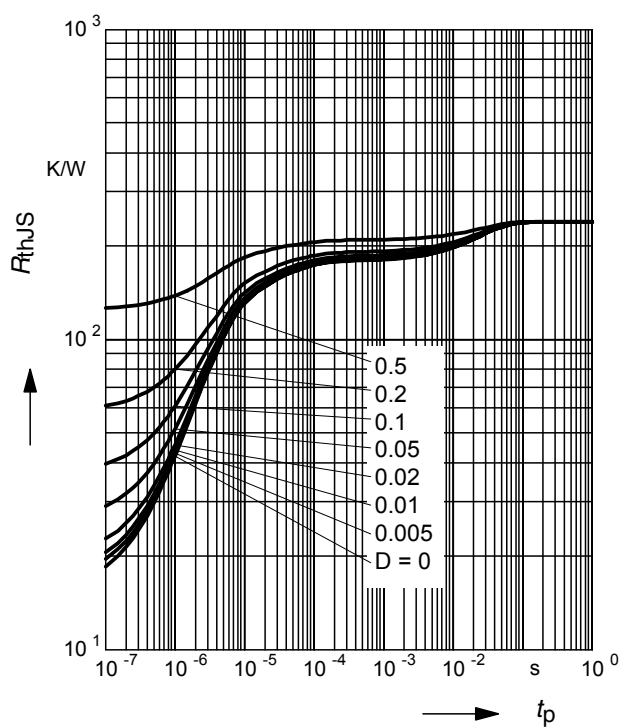
For examples and ready to use parameters please contact your local Infineon Technologies distributor or sales office to obtain a Infineon Technologies CD-ROM or see Internet: <http://www.infineon.com/products/discrete/index.htm>

**Total power dissipation**  $P_{\text{tot}} = f(T_A^*, T_S)$

\* Package mounted on epoxy

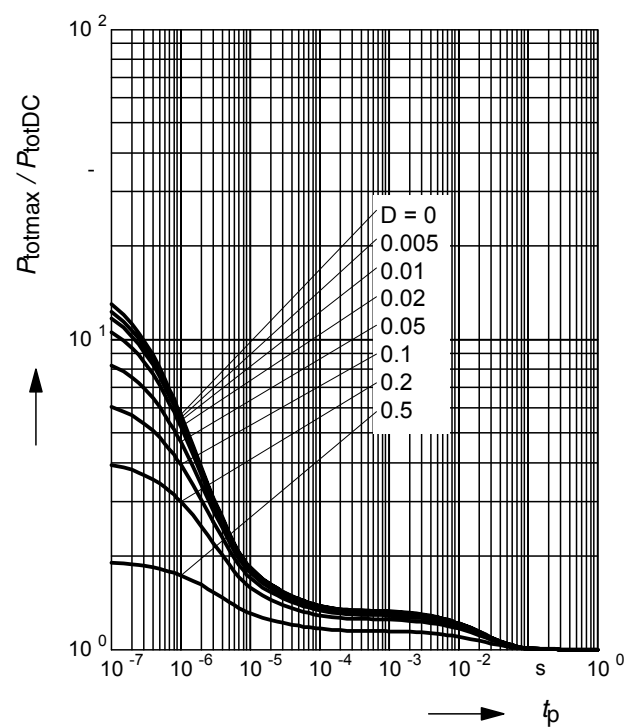


**Permissible Pulse Load**  $R_{\text{thJS}} = f(t_p)$



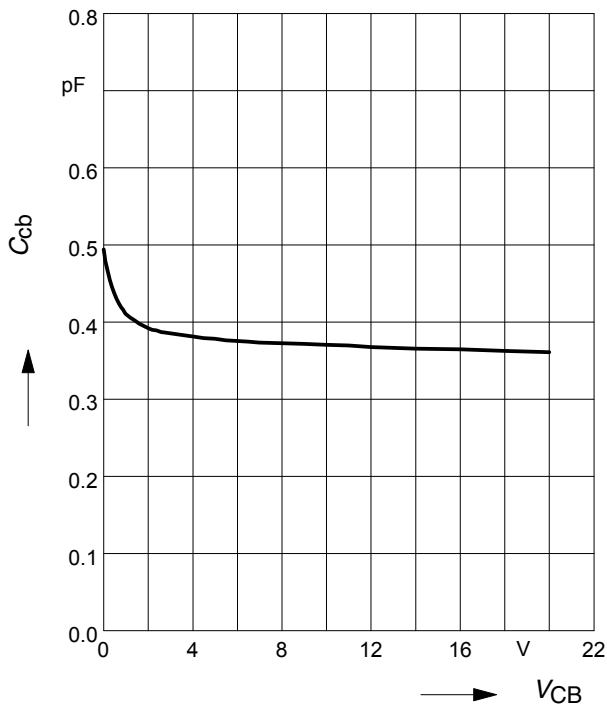
**Permissible Pulse Load**

$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$



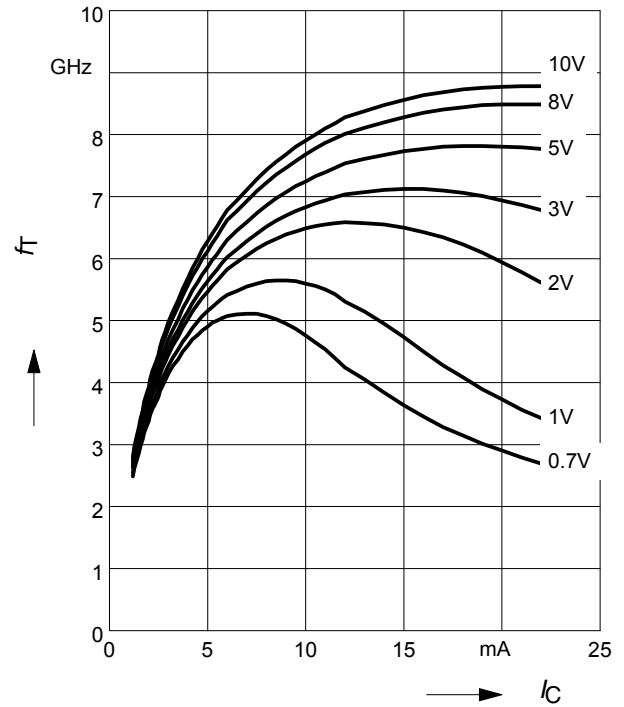
**Collector-base capacitance**  $C_{cb} = f(V_{CB})$

$f = 1\text{MHz}$



**Transition frequency**  $f_T = f(I_C)$

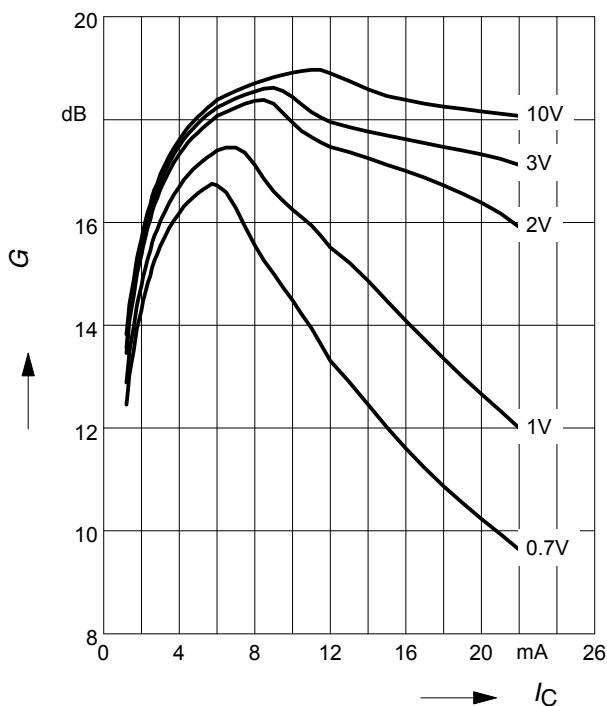
$V_{CE} = \text{Parameter}$



**Power Gain**  $G_{ma}, G_{ms} = f(I_C)$

$f = 0.9\text{GHz}$

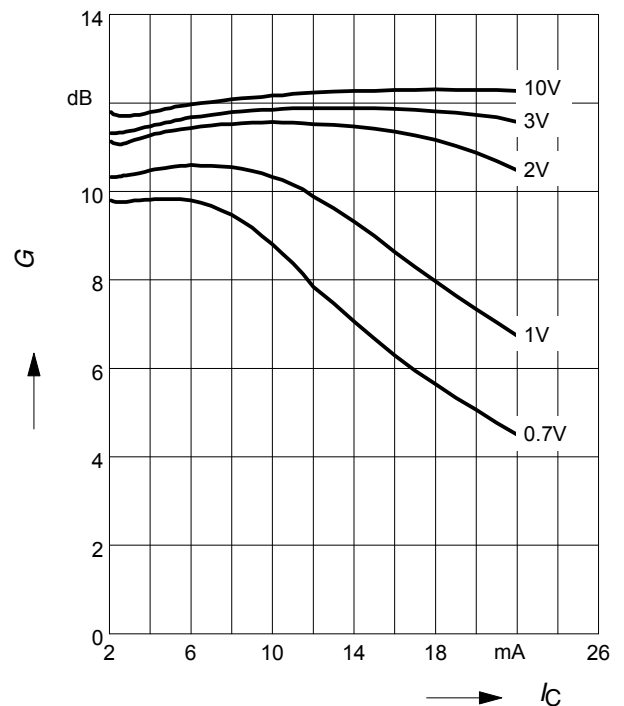
$V_{CE} = \text{Parameter}$



**Power Gain**  $G_{ma}, G_{ms} = f(I_C)$

$f = 1.8\text{GHz}$

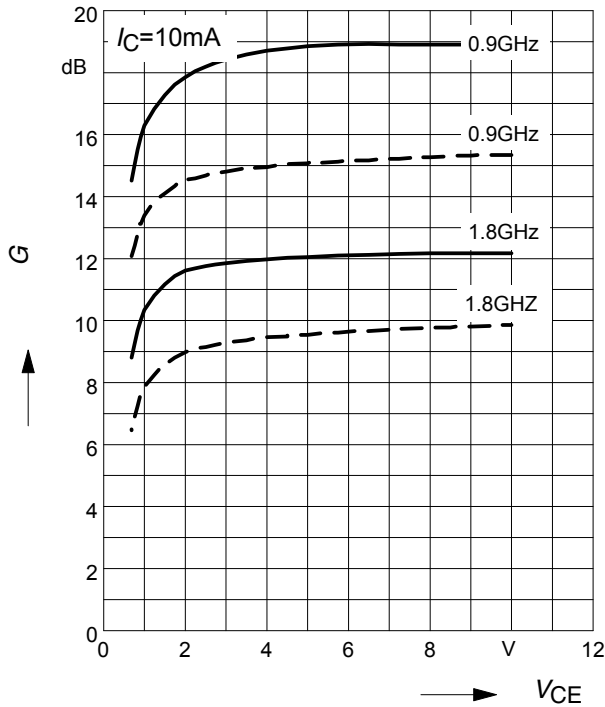
$V_{CE} = \text{Parameter}$



**Power Gain**  $G_{ma}, G_{ms} = f(V_{CE})$ :

$|S_{21}|^2 = f(V_{CE})$ :

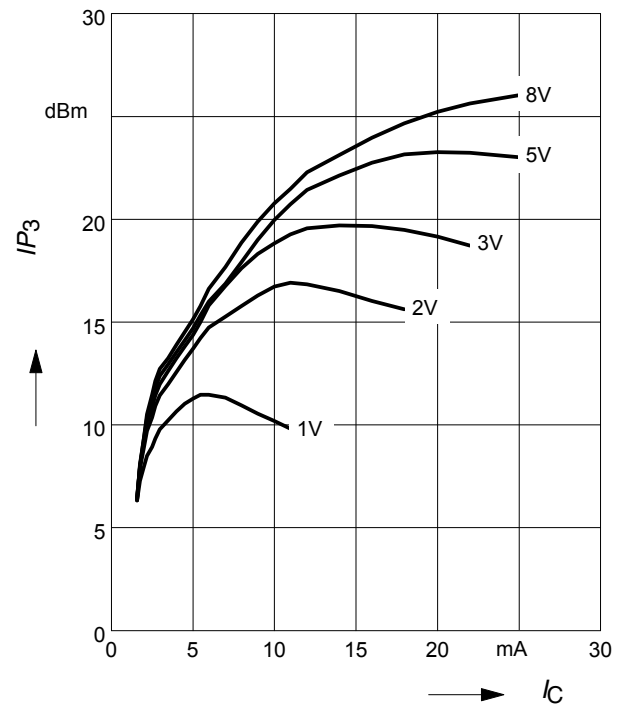
$f$  = Parameter



**Intermodulation Intercept Point**  $IP_3 = f(I_C)$

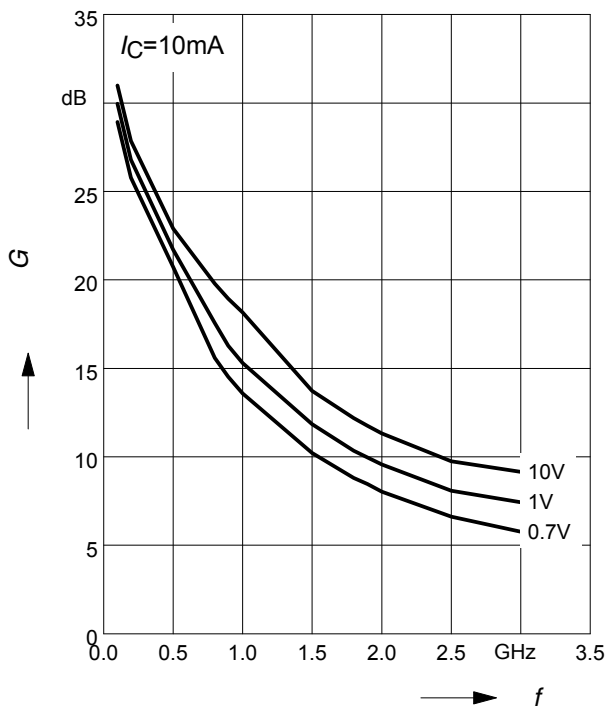
(3rd order, Output,  $Z_S = Z_L = 50\Omega$ )

$V_{CE}$  = Parameter,  $f = 900\text{MHz}$



**Power Gain**  $G_{ma}, G_{ms} = f(f)$

$V_{CE}$  = Parameter



**Power Gain**  $|S_{21}|^2 = f(f)$

$V_{CE}$  = Parameter

